

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (DARLINGTON POWER)

2SD1409A

IGNITER APPLICATIONS.

HIGH VOLTAGE SWITCHING APPLICATIONS.

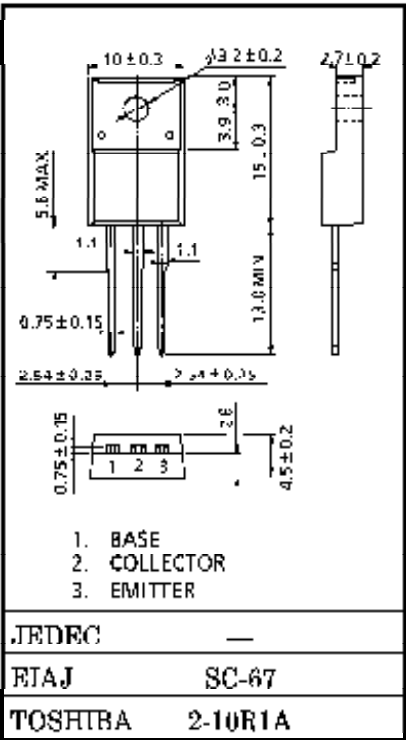
- High DC Current Gain : $h_{FE} = 600$ (Min.) ($V_{CE} = 2V$, $I_C = 2A$)
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	6	A
Base Current	I_B	1	A
Collector Power Dissipation	P_C	2.0	W
		25	
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

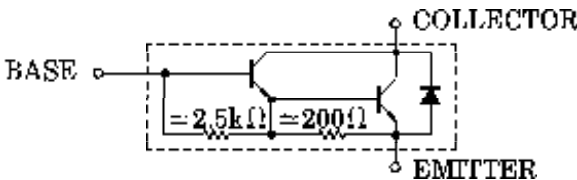
INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 1.7g

EQUIVALENT CIRCUIT



96100-7431

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ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=800V, I_E=0$	—	—	0.5	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	—	—	3	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CBO}$	$I_C=10mA, I_B=0$	400	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE}=2V, I_C=2A$	600	—	—	
		$h_{FE(2)}$	$V_{CE}=2V, I_C=4A$	100	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=4A, I_B=0.04A$	—	—	2.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C=4A, I_B=0.04A$	—	—	2.5	V
Emitter-Collector Forward Voltage		V_{ECF}	$I_E=4A, I_B=0$	—	—	3.0	V
Collector Output Capacitance		C_{ob}	$V_{CB}=50V, I_E=0, f=1MHz$	—	35	—	pF
Switching Time	Turn-on Time	t_{on}	$I_{B1} = -I_{B2} = 0.04A$, DUTY CYCLE $< 1\%$	—	1	—	μs
	Storage Time	t_{str}		—	8	—	
	Fall Time	t_f		—	5	—	

